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FØRM PTO-1449				Docket Number (Optional) 81839.0108		Application Number Not Assigned		2
INF	ORMATION DISCLOSURE IN AN APPLICATIO	Applicant Takehito USHIKI; Hitoshi TSUNODA						
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE		NAME	E CLASS SUBCLASS		FILING DATE IF APPROPRIATE	
92	5,447,890	09/1995	Kato	et al.	437	249		
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YD	∴ EP 0782179	7/02/1997		EPO			YES	NO
i	, EP 0337556	10/18/1989		EPO			x	
	. WO 8912318	12/14/1989		PCT			×	
	₽ EP 0764976	03/26/1997		EPO			x	
2L	→ JP06-114664	04/26/1994		JAPAN			Abstract	
	OTHER DOCUME	NTS (Including A	uthor,	Title, Date, Per	tinent Pages.	Etc.)	I	
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EXAMINER .	Id	DATE CONSIDERED	5/14/03	

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.